

43.(Amended) A contact hole for a semiconductor device, comprising:

- a bottom surface of a first material;
- at least one vertical sidewall of a second material;
- a layer of a third material covering only the bottom surface with a thickness variation of less than 50%, the third material including at least two different constituent elements.

48.(Amended) A contact hole for a semiconductor device, comprising:

- a bottom surface of a first material;
- at least one vertical sidewall of a second material;
- a generally planar layer of a third material covering only the bottom surface, the third material having a graded stoichiometry between two different elements.

55.(Amended) A contact hole for a semiconductor device, comprising:

- a bottom surface of a first material;
- at least one sidewall of an insulating material;
- a generally planar layer of a third material covering only the bottom surface, the third material including at least two different constituent elements, none of the third material being present in the sidewall.

59.(Amended) An integrated circuit, comprising:

- a substrate of a first material;
- an insulator of a second material overlying the substrate;
- a [multiple] contact hole[s] through the insulator to the substrate, [each] the contact hole having at least one sidewall of the second material and a generally planar conductive layer located only in a region contacting the substrate, the layer including at least two different constituent elements.

63.(Amended) The integrated circuit of claim 59 where the layer is planar within a thickness variation less than 50%.